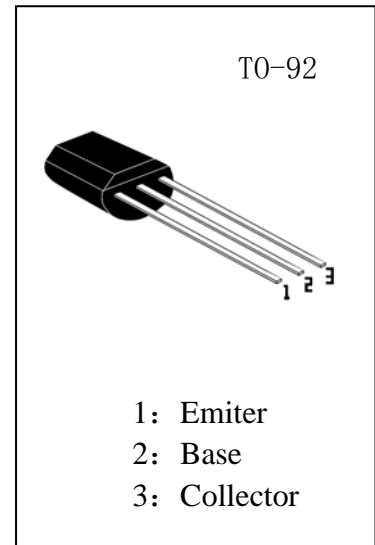


高压晶体管

- $V_{ce} = -400V$
- 低饱和电压
- 与 MPSA94 对管

极限参数(Absolute Maximum Ratings) $T_a = 25^{\circ}C$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	400	V
Collector-Emitter Voltage	V_{ceo}	400	V
Emitter-Base Voltage	V_{ebo}	6	V
Collector Current	I_c	300	mA
Collector Dissipation	P_c	625	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~150	$^{\circ}C$



电性能(Electrical Characteristic) $T_a = 25^{\circ}C$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c = 100\mu A, I_e = 0$	400			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c = 1mA, I_b = 0$	400			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e = 100\mu A, I_c = 0$	6			V
I_{cbo}	Collector Cutoff Current	$V_{cb} = 400V, I_e = 0$			100	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb} = 4V, I_c = 0$			100	nA
I_{ces}	Collector Cutoff Current	$V_{ce} = 400V, V_{eb} = 0$			0.5	μA
$V_{ce(sat)1}$	Collector-Emitter Saturation Voltage	$I_c = 1mA, I_b = 0.1mA$			0.4	V
$V_{ce(sat)1}$	Collector-Emitter Saturation Voltage	$I_c = 10mA, I_b = 1mA$			0.5	V
$V_{ce(sat)2}$	Collector-Emitter Saturation Voltage	$I_c = 50mA, I_b = 5mA$			0.75	V
$V_{be(sat)}$	Base-Emitter Saturation Voltage	$I_c = 10mA, I_b = 1mA$			0.75	V
H_{fe1}	DC Current Gain	$V_{ce} = 10V, I_c = 1mA$	40			
H_{fe2}	DC Current Gain	$V_{ce} = 10V, I_c = 10mA$	50		300	
H_{fe3}	DC Current Gain	$V_{ce} = 10V, I_c = 50mA$	45			
H_{fe4}	DC Current Gain	$V_{ce} = 10V, I_c = 100mA$	40			
C_{ob}	Output Capacitance	$V_{cb} = 20V, I_e = 0, f = 1MHz$			7	PF
f_T	Current Gain-Bandwidth product	$V_{ce} = 20V, I_c = 10mA$	50			MHz

Class	B	C	D	E
Hfe2	50-80	80-150	150-200	200-300